

SuperMOS – SOT-723 20V V_{DSS} , 200m Ω $R_{DS(ON)}$, N-channel MOSFET

1. Description

The NTK3134NT1G-ES is N-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product NTK3134NT1G-ES is Pb-free.

2. Features

- 20V, $R_{DS(ON)}=200m\Omega(Typ.) @ V_{GS}=4.5V$
- $R_{DS(ON)}=290m\Omega(Typ.) @V_{GS}=2.5V$
- $R_{DS(ON)}=480m\Omega(Typ.) @V_{GS}=1.8V$
- Use trench MOSFET technology
- High density cell design for low $R_{DS(on)}$
- Material: Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current

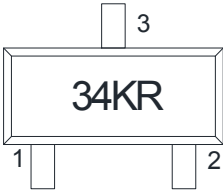
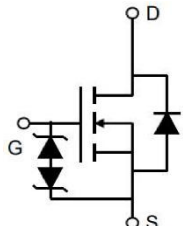
3. Applications

- PWM applications
- Load switch
- Power management in portable/desktop PCs
- DC/DC conversion

4. Ordering Information

Part Number	Package	Marking	Material	Packing	Quantity per reel	Flammability Rating	Reel Size
NTK3134NT1G-ES	SOT-723	34KR	Halogen free	Tape & Reel	8,000 PCS	UL 94V-0	7 inches

5. Pin Configuration and Functions

Pin	Function	Outline	Circuit Diagram
1	Gate		
2	Source		
3	Drain		

6. Specification

Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	BV_{DSS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	$T_A=25^\circ\text{C}$	0.7
		$T_A=75^\circ\text{C}$	0.54
Maximum Power Dissipation	P_D	0.22	W
Pulsed Drain Current	I_{DM}	2.8	A
Operating Junction Temperature	T_J	150	$^\circ\text{C}$
Lead Temperature	T_L	260	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 150	$^\circ\text{C}$

Thermal resistance ratings

Single Operation					
Parameter		Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance	$t \leq 10\text{s}$	$R_{\theta JA}$		556	$^\circ\text{C/W}$

Electrical Characteristics

At TA = 25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$			1	μA
Gate-to-source Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 10V$			± 10	μA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	0.35	0.75	1.10	V
Drain-to-source On-resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=0.5A$		200	300	m Ω
		$V_{GS}=2.5V, I_D=0.4A$		290	400	
		$V_{GS}=1.8V, I_D=0.2A$		480	700	
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C_{ISS}	$V_{GS}=0V, f=1MHz,$ $V_{DS}=10V$		56		pF
Output Capacitance	C_{OSS}			20		
Reverse Transfer Capacitance	C_{RSS}			2.5		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS}=4.5V, V_{DS}=10V,$ $I_D=0.5A$		1		nC
Gate-to-Source Charge	Q_{GS}			0.28		
Gate-to-Drain Charge	Q_{GD}			0.22		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS}=4.5V, V_{DS}=10V,$ $I_D=0.5A, R_G=10\Omega$		2		ns
Rise Time	t_r			18.8		
Turn-Off Delay Time	$t_{d(OFF)}$			10		
Fall Time	t_f			23		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=0.5A$			1.2	V

7. Typical Characteristic

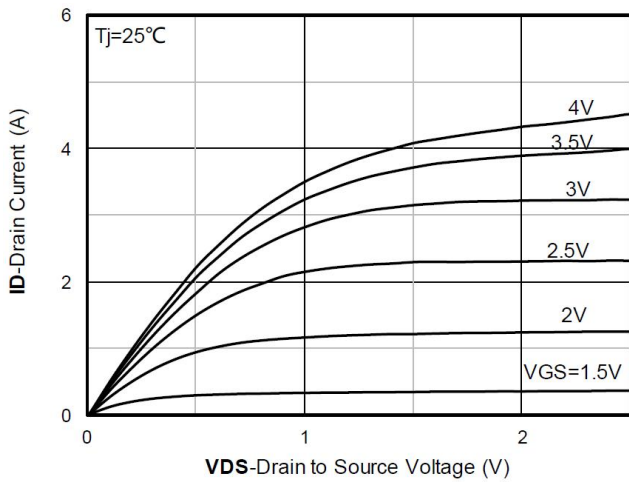


Figure1. Output Characteristics

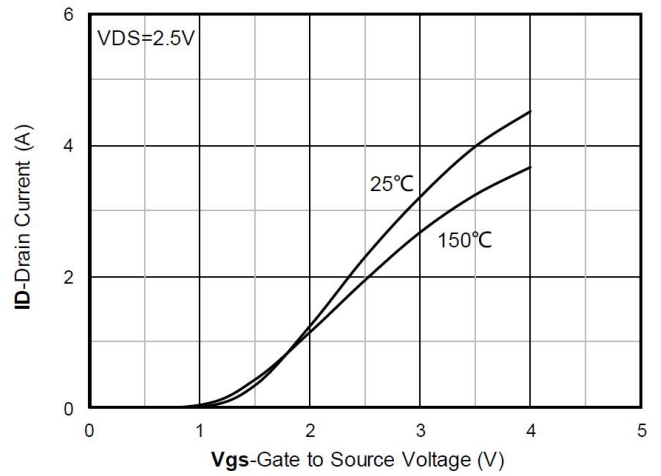


Figure2. Transfer Characteristics

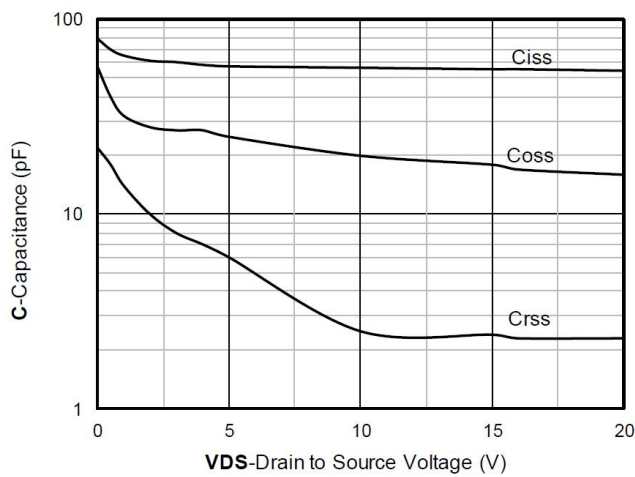


Figure3. Capacitance Characteristics

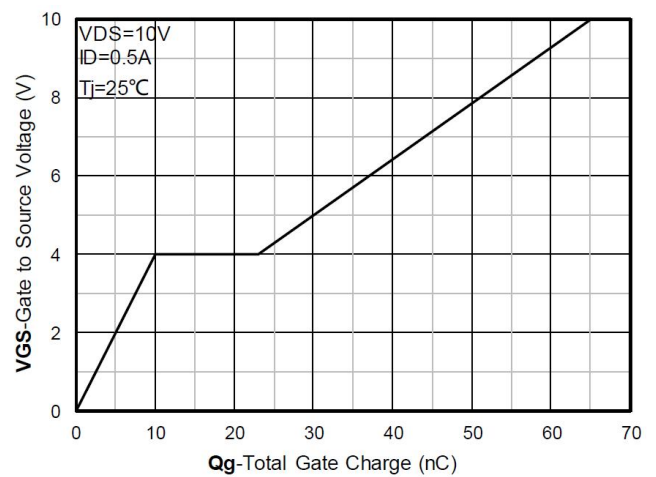


Figure4. Gate Charge

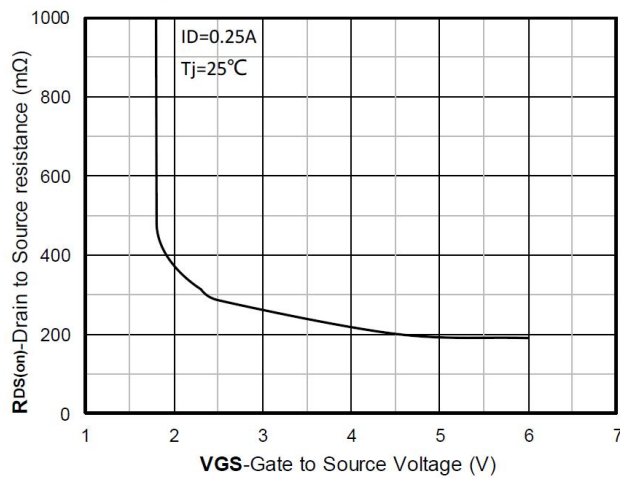


Figure5. On-Resistance vs Gate to Source Voltage

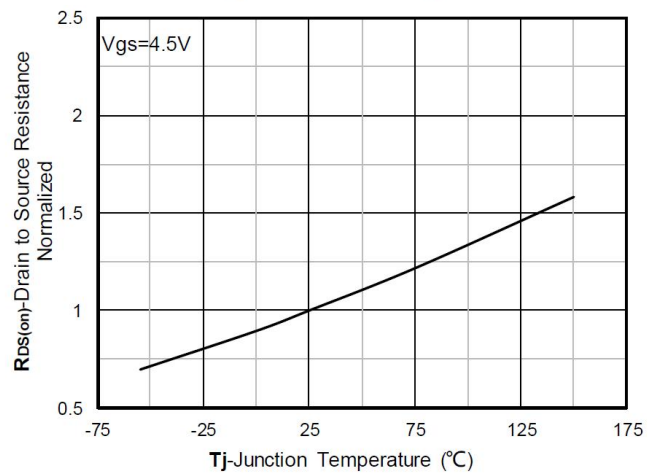


Figure6. Normalized On-Resistance

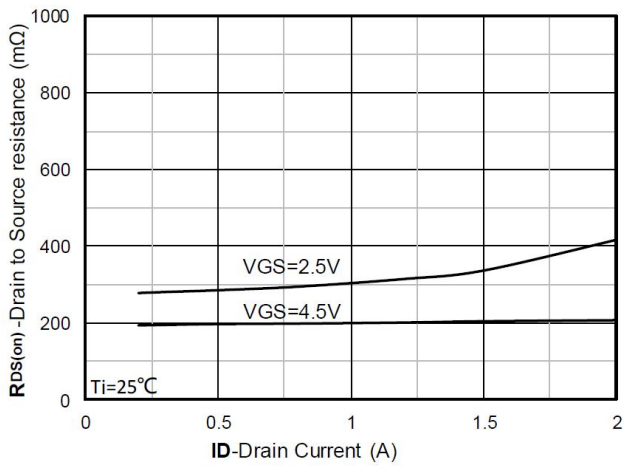


Figure7. RDS(on) VS Drain Current

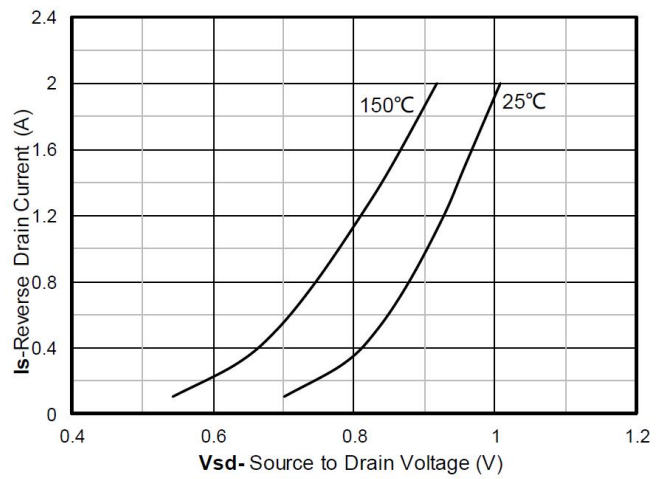


Figure8. Forward characteristics of reverse diode

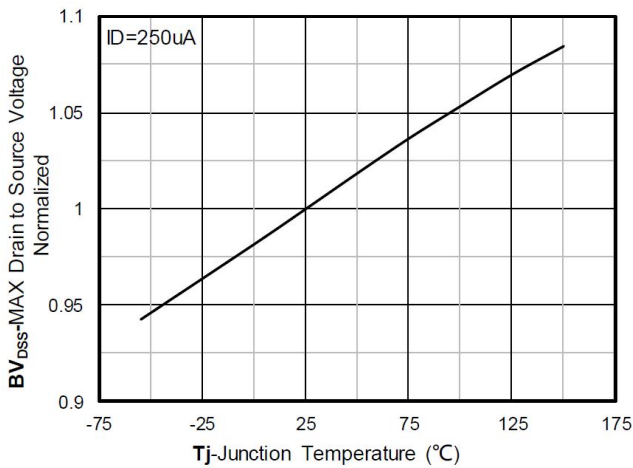


Figure9. Normalized breakdown voltage

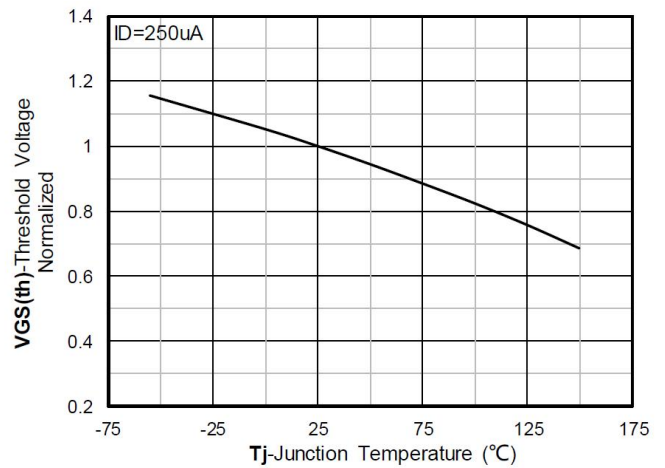


Figure10. Normalized Threshold voltage

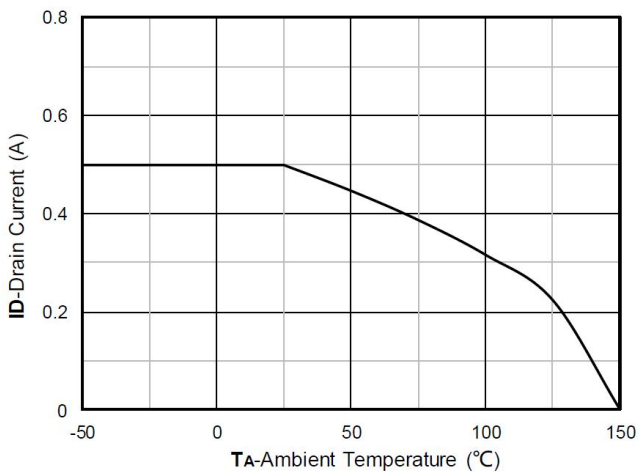


Figure11. Current dissipation

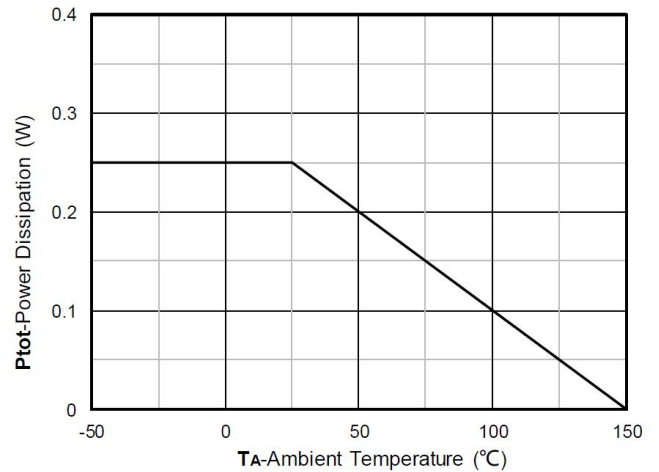


Figure12. Power dissipation

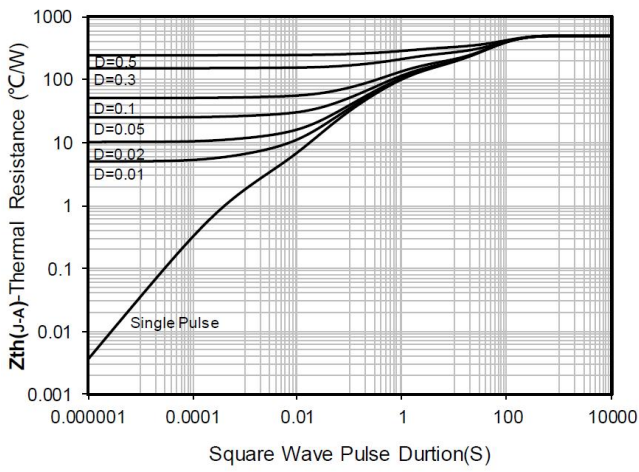


Figure 13. Maximum Transient Thermal Impedance

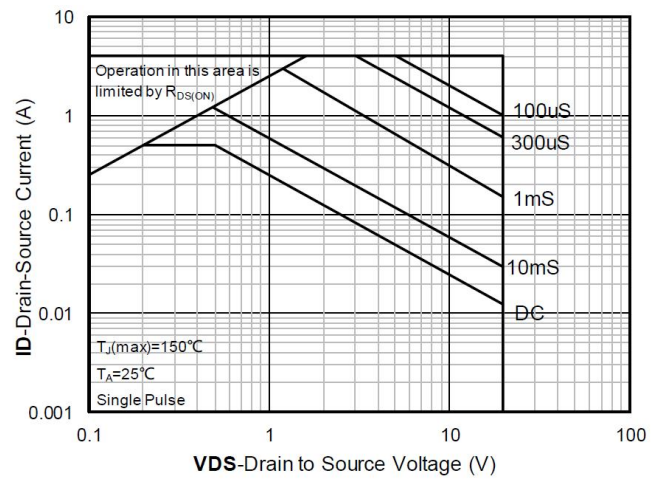
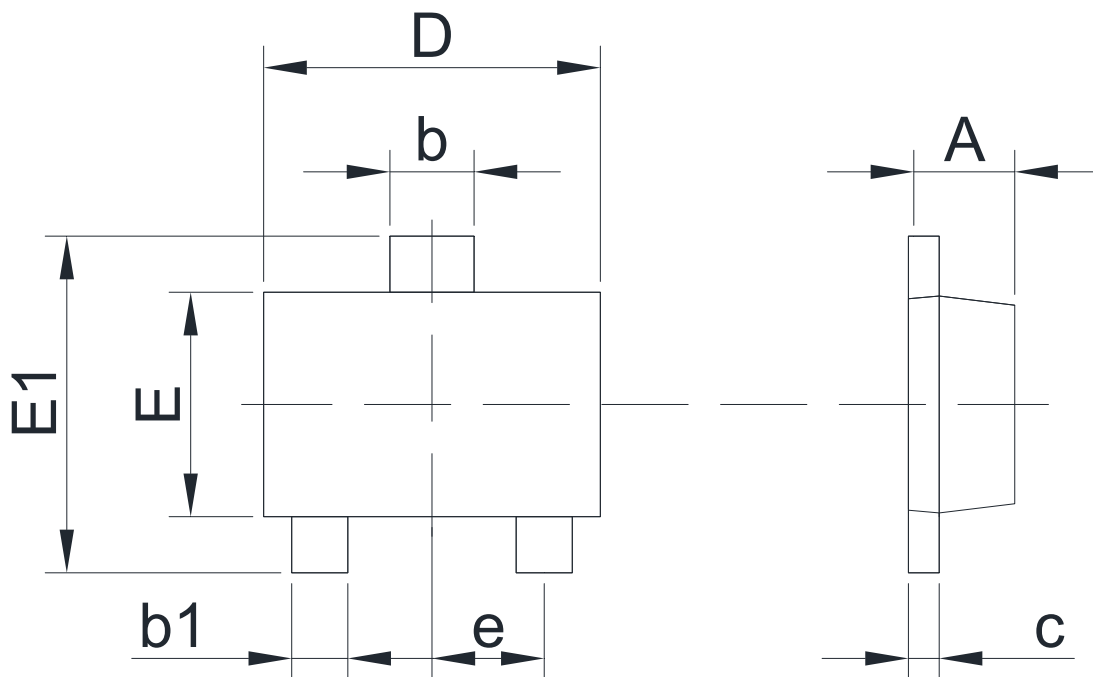


Figure14. Safe Operation Area

8. Dimension (SOT-723)



Dimensions in Millimeters					
Symbol	Min.	Max.	Symbol	Min.	Max.
A	0.37	0.50	D	1.10	1.30
b	0.20	0.30	E	0.70	0.90
b1	0.15	0.25	E1	1.05	1.35
c	0.06	0.16	e	0.400REF	

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